

Semiconductors
High-reliability discrete products and engineering services since 1977

## 2SD869

## NPN POWER TRANSISTORS

## FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS ( $\mathrm{Sn} / \mathrm{Pb}$ plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

| Characteristic | Symbol | 2SD869 | Unit |
| :--- | :---: | :---: | :---: |
| Collector-Emitter Voltage | $\mathrm{V}_{\text {СЕО }}$ | 600 | V |
| Collector-Emitter Voltage | $\mathrm{V}_{\text {СBO }}$ | 1500 | V |
| Emitter-Base Voltage | $\mathrm{V}_{\text {EBO }}$ | 5.0 | V |
| Collector Current - continuous | $\mathrm{I}_{\mathrm{C}}$ | 3.5 | A |
| Emitter Current -continuous | $\mathrm{I}_{\mathrm{E}}$ | -3.5 | A |
| Total Power Dissipation @ $\mathrm{T}_{\mathbf{C}}=\mathbf{2 5}^{\circ} \mathbf{C}$ | $\mathrm{P}_{\mathrm{D}}$ | 50 | W |
| Operating and Storage Temperature Range | $\mathrm{T}_{\mathrm{J},} \mathrm{T}_{\text {stg }}$ | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |

ELECTRICAL CHARACTERISTICS ( $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ unless otherwise specified)

| Characteristic | Symbol | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Collector Cutoff Current $\left(\mathrm{V}_{\mathrm{CB}}=500 \mathrm{~V}, \mathrm{I}_{\mathrm{E}}=0\right)$ | Icbo | - | - | 5 | $\mu \mathrm{A}$ |
| Emitter Base Breakdown Voltage $\left(\mathrm{I}_{\mathrm{E}}=200 \mathrm{~mA}, \mathrm{I}_{\mathrm{C}}=0\right)$ | $\mathrm{V}_{\text {Br(EbO) }}$ | 5 | - | - | V |
| DC Current Gain $\left(\mathrm{IC}=0.5 \mathrm{~A}, \mathrm{~V}_{\mathrm{CE}}=5.0 \mathrm{~V}\right)$ | $\mathrm{h}_{\mathrm{FE}}$ | 8 | 12 | - | - |
| Collector-Emitter Saturation Voltage $\left(I_{C}=3.0 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=0.8 \mathrm{~A}\right)$ | $\mathrm{V}_{\text {CE(sat) }}$ | - | 5 | 8 | V |
| Base-Emitter Saturation Voltage $\left(\mathrm{I}_{\mathrm{C}}=3.0 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=0.8 \mathrm{~A}\right)$ | $\mathrm{V}_{\text {BE (sat) }}$ | - | - | 1.5 | V |
| Forward Voltage (Damper Diode) $\left(I_{F}=3 A\right)$ | $-V_{F}$ | - | . 6 | 2.0 | V |
| Transition Frequency $\left(\mathrm{V}_{\mathrm{CE}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=0.1 \mathrm{~A}\right)$ | $\mathrm{f}_{\mathrm{T}}$ | - | 3 | - | MHz |
| Collector Output Capacitance $\left(\mathrm{V}_{\mathrm{CB}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{E}}=0, \mathrm{f}=1.0 \mathrm{kHz}\right)$ | Cob | - | 95 | - | pF |
| Fall Time $\left(I_{C P}=3 \mathrm{~A}, I_{B 1(\text { end })}=0.8 \mathrm{~A}\right)$ | $\mathrm{t}_{\mathrm{f}}$ | - | 0.5 | 1.0 | $\mu \mathrm{s}$ |



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MECHANICAL CHARACTERISTICS

| Case: | TO-3 |
| :--- | :--- |
| Marking: | Alpha-Numeric |
| Polarity: | See below |


|  | TO-3 |  |  |  |
| :---: | :---: | :---: | :---: | :---: |
|  | Inches |  | Millimeters |  |
|  | Min | Max | Min | Max |
| CD | - | 0.875 | - | 22.220 |
| CH | 0.250 | 0.380 | 6.860 | 9.650 |
| HT | 0.060 | 0.135 | 1.520 | 3.430 |
| BW | - | 1.050 | - | 26.670 |
| HD | 0.131 | 0.188 | 3.330 | 4.780 |
| LD | 0.038 | 0.043 | 0.970 | 1.090 |
| LL | 0.312 | 0.500 | 7.920 | 12.700 |
| BL | 1.550 | REF | 39.370 | REF |
| MHS | 1.177 | 1.197 | 29.900 | 30.400 |
| PS | 0.420 | 0.440 | 10.670 | 11.180 |
| S1 | 0.655 | 0.675 | 16.640 | 17.150 |

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Fig. $\quad t_{f}$ TEST CIRCUIT


## ${ }^{-2}$ IGITRON Semiconductors

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